



Product: Bridge Rectifiers (In Line)

Bridge Rectifiers are key devices in many applications where a rectifier signal is required as Input voltage. Linear Power Supplies, SMPS, Battery Chargers, Electronic Ballast... are some applications where they are used.

Manufactured using HYPERRECTIFIER® technology, we offer these devices in several different packages: SMD, Dual In Line, Round, In Line and Square Power.

Product	Family	$I_{F(AV)}$ (A)	I_{FSM} (A)	V_{RRM} (V)	V_F (V)	OUTLINE
FBI6J1M1	FBI6-1M1	6.0	170	600	1.05	In Line medium

6 Amp. Glass Passivated Bridge Rectifier

<p>Dimensions in mm.</p> <p>Plastic Case</p> <table border="1"> <thead> <tr> <th>L</th> <th>suffix</th> </tr> </thead> <tbody> <tr> <td>17.5</td> <td></td> </tr> <tr> <td>8</td> <td>-4</td> </tr> </tbody> </table> <ul style="list-style-type: none"> • Mounting Instructions • High temperature soldering guaranteed: 260 °C – 10 sc. • Recommended mounting torque: 8 Kg.cm. 	L	suffix	17.5		8	-4	<p>Voltage 50 to 1000 V.</p> <p>Current 6.0 A.</p>
L	suffix						
17.5							
8	-4						
<ul style="list-style-type: none"> • Glass Passivated Junction Chips. • UL recognized under component index file number E320541. • Lead and polarity identifications. • Case: Molded Plastic. • Ideal for printed circuit board (P.C.B.). • High surge current capability. • The plastic material carries U/L recognition 94 V-O. 							

Maximum Ratings, according to IEC publication No. 134

		FBI6A 1M1	FBI6B 1M1	FBI6D 1M1	FBI6G 1M1	FBI6J 1M1	FBI6K 1M1	FBI6M 1M1
V_{RRM}	Peak recurrent reverse voltage (V)	50	100	200	400	600	800	1000
V_{RMS}	Maximum RMS voltage (V)	35	70	140	280	420	560	700
$I_{F(AV)}$	Max. Average forward current with heatsink without heatsink	6.0 A at 100 °C 3.0 A at 40 °C						
I_{FSM}	10 ms. peak forward surge current (Jedec Method)	170 A						
I^2t	Current squared time (rating for fusing) (1ms.<t<10ms. Tc = 25°C)	140 A ² sec						
V_{DIS}	Dielectric strength (terminals to case, AC 1 min.)	2000 V						
T_j	Operating temperature range	– 55 to + 150 °C						
T_{stg}	Storage temperature range	– 55 to +150 °C						

Electrical Characteristics at Tamb = 25°C

V_F	Max. forward voltage drop per diode at $I_F = 3.0 A$	1.05 V
I_R	Max. instantaneous reverse current at V_{RRM}	5 μA
$R_{th(j-c)}$	MAXIMUM THERMAL RESISTANCE Junction-Case. With Heatsink.	2.2 °C/W
$R_{th(j-a)}$	Junction-Ambient. Without Heatsink.	22 °C/W